

RoHS

HALOGEN

FRFF



Improved Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441B, DG442B are monolithic quad analog switches designed to provide high speed, low error switching of analog and audio signals. The DG441B, DG442B are upgrades to the original DG441, DG442.

Combing low on-resistance (45 Ω , typ.) with high speed (t_{ON} 120 ns, typ.), the DG441B, DG442B are ideally suited for Data Acquisition, Communication Systems, Automatic Test Equipment, or Medical Instrumentation. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

The DG441B, DG442B are built using Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

When on, each switch conducts equally well in both directions and blocks input voltages to the supply levels when off.

FEATURES

- Low On-Resistance: 45 Ω
- Low Power Consumption: 1 mW
- Fast Switching Action t_{ON}: 120 ns
- Low Charge Injection Q: 1 pC
- TTL/CMOS-Compatible Logic
- Single Supply Capability
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

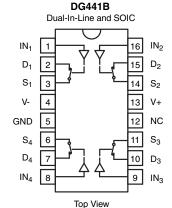
BENEFITS

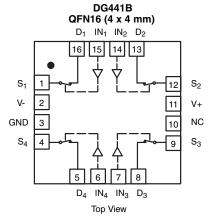
- Less Signal Errors and Distortion
- Reduced Power Supply Requirements
- Faster Throughput
- Reduced Pedestal Errors
- Simple Interfacing

APPLICATIONS

- Audio Switching
- **Data Acquisition**
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- **Medical Instruments**

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE								
Logic	DG441B	DG442B						
0	ON	OFF						
1	OFF	ON						

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION								
Temp Range	Package	Part Number						
		DG441BDJ						
	16-pin Plastic DIP	DG441BDJ-E3						
	10-pii11 lastic Dii	DG442BDJ						
		DG442BDJ-E3						
- 40 °C to 85 °C		DG441BDY-E3						
- 40 0 10 05 0	16-pin Narrow SOIC	DG441BDY-T1-E3						
	10-piii Nariow 3010	DG442BDY-E3						
		DG442BDY-T1-E3						
	16 pin QFN 4 x 4 mm	DG441BDN-T1-E4						
	(Variation 1)	DG442BDN-T1-E4						

DG441B, DG442B

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter		Symbol	Limit	Unit				
V+ to V-			44					
GND to V-			25	V				
Digital Inputs ^a , V_S , V_D			(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first					
Continuous Current (Any Termina	al)		30	mA				
Current, S or D (Pulsed at 1 ms,	10 % duty cycle)		100] IIIA				
Storage Temperature			- 65 to 125	°C				
	16-pin Plastic DIP ^c		470					
Power Dissipation (Package) ^b	16-pin Narrow Body SOIC ^d		900	mW				
	QFN-16 ^d		850					

a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6 mW/°C above 75 °C.

d. Derate 12 mW/°C above 75 °C.



		Test Conditions				Limits			
		Unless Otherwise Specified		- 40 °C to 85 °C					
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^e$	Temp.b	Min. ^d	Typ. ^c	Max. ^d	Unit		
Analog Switch			<u> </u>		I.	1			
Analog Signal Range ^e	V _{ANALOG}		Full	- 15		15	V		
Drain-Source On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full		45	80 95	Ω		
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full		2	4 5	5.2		
Switch Off Leakage Current	I _{S(off)}	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5			
owner on Leanage ourient	I _{D(off)}	.0, .5	Room Full	- 0.5 - 5	± 0.01	0.5 5	nA		
Channel On Leakage Current	I _{D(on)}	$V_S = V_D = \pm 14 \text{ V}$	Room Full	- 0.5 - 10	± 0.02	0.5 10			
Digital Control									
Input Voltage Low	V _{INL}		Full			0.8	V		
Input Voltage High	V _{INH}		Full	2.4			•		
Input Current V _{IN} Low	I _{INL}	V _{IN} under test = 0.8 V All Other = 2.4 V	Full	- 1	- 0.01	1	μΑ		
Input Current V _{IN} High	I _{INH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	- 1	0.01	1			
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room		120	220	ns		
Turn-Off Time	t _{OFF}	$V_S = 10 V$, See Figure 2	Room		65	120	115		
Charge Injection ^e	Q	$C_L = 1 \text{ nF, } V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room		- 1		рС		
Off Isolation ^e	OIRR	$R_L = 50 \Omega$, $C_L = 15 pF$	Room		- 90		40		
Crosstalk (Channel-to-Channel)	X _{TALK}	$V_S = 1 V_{RMS}$, $f = 100 kHz$	Room		- 95		dB		
SourceOff Capacitance ^e	C _{S(off)}	f 1 MI I-	Room		4				
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room		4		pF		
Channel On Capacitance ^e	C _{D(on)}	$V_S = V_D = 0 V$, $f = 1 MHz$	Room		16				
Power Supplies	,								
Positive Supply Current	I+	V+ = 16.5 V, V- = - 16.5 V	Room Full			1 5	^		
Negative Supply Current	I-	$V_{IN} = 0 \text{ or } 5 \text{ V}$	Room Full	- 1 - 5			- μΑ		



SPECIFICATIONS (for single supply)									
		Test Conditions Unless Otherwise Specified V+ = 12 V, V- = 0 V		Limits - 40 °C to 85 °C					
Parameter	Symbol	$V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{e}$	Temp.b	Min. ^d	Typ. ^c	Max. ^d	Unit		
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full	0		12	V		
Drain-Source On-Resistance	R _{DS(on)}	I _S = 1 mA, V _D = 3 V, 8 V	Room Full		90	160 200	Ω		
Dynamic Characteristics			•						
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}, V_S = 8 \text{ V}$	Room		120	300	ns		
Turn-Off Time	t _{OFF}	See Figure 2	Room		60	200	115		
Charge Injection	Q	$C_L = 1 \text{ nF, } V_{gen} = 6 \text{ V, } R_{gen} = 0 \Omega$	Room		4		рC		
Power Supplies									
Positive Supply Current	l+	V _{IN} = 0 V or 5 V	Room Full			1 5	μΑ		
Negative Supply Current	l-	V _{IN} = 0 V OI 0 V	Room Full	- 1 - 5			μΑ		

Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SCHEMATIC DIAGRAM (typical channel)

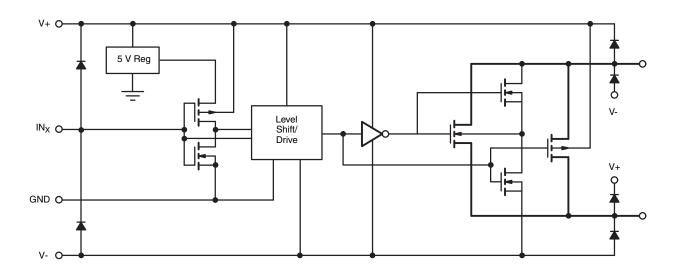
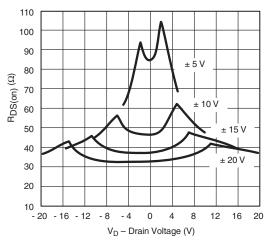


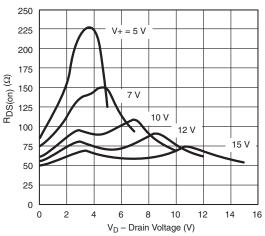
Figure 1.



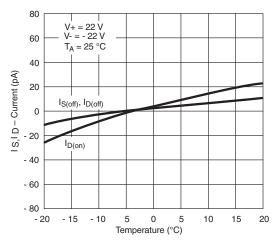
TYPICAL CHARACTERISTICS $(T_A = 25 \, ^{\circ}\text{C}, \text{ unless otherwise noted})$



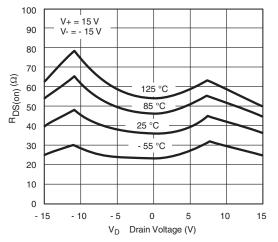
 $R_{DS(on)}$ vs. V_D and Power Supply Voltages



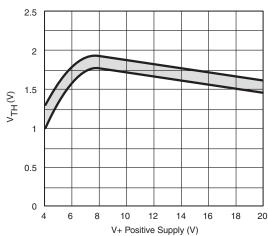
R_{DS(on)} vs. V_D and Single Power Supply Voltages



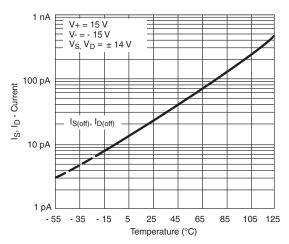
Leakage Currents vs. Analog Voltage



 $R_{DS(on)}$ vs. V_D and Temperature

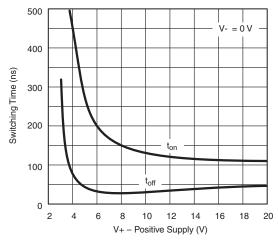


Input Switching Threshold vs. Supply Voltage

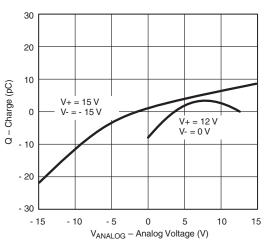


Leakage Currents vs. Temperature

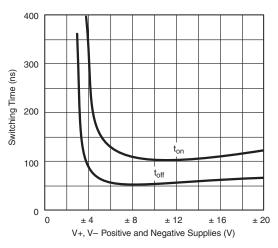
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



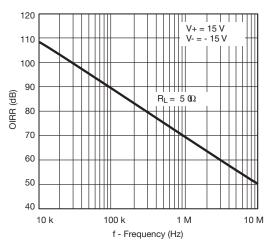
Switching Time vs. Single Supply Voltage



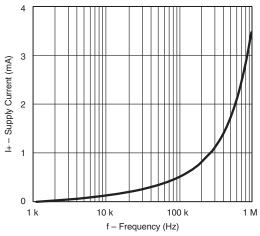
 $\mathbf{Q_S},\,\mathbf{Q_D}$ - Charge Injection vs. Analog Voltage



Switching Times vs. Power Supply Voltage

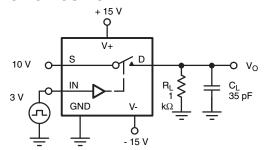


Off Isolation vs. Frequency

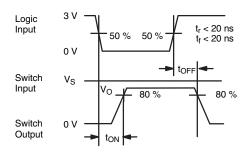


Supply Current vs. Switching Frequency

TEST CIRCUITS

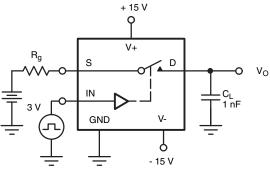


C_L (includes fixture and stray capacitance)



Note: Logic input waveform is inverted for DG442.

Figure 2. Switching Time



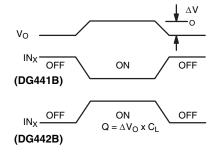
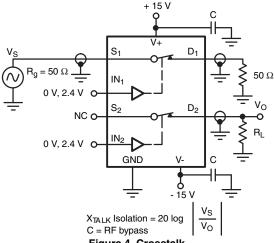
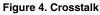


Figure 3. Charge Injection

C = 1 mF tantalum in parallel with 0.01 mF ceramic





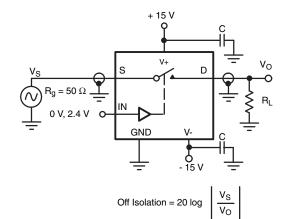


Figure 5. Off Isolation

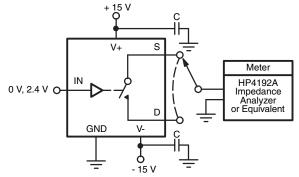
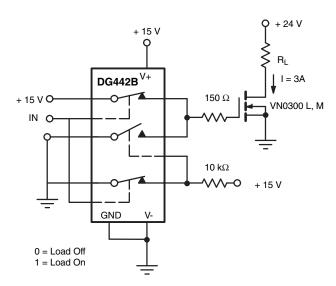


Figure 6. Source/Drain Capacitances

APPLICATIONS





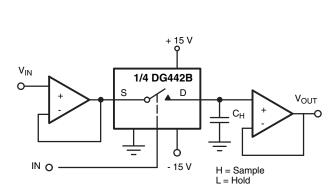


Figure 7. Power MOSFET Driver

Figure 8. Open Loop Sample-and-Hold

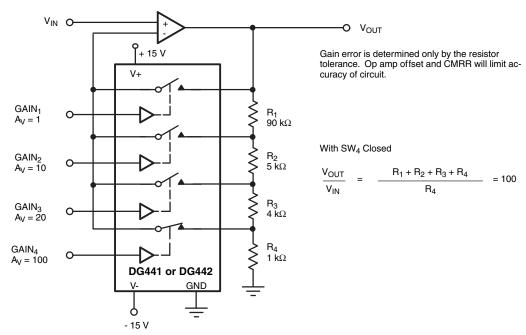
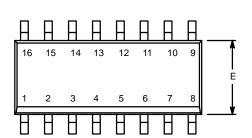


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72625.

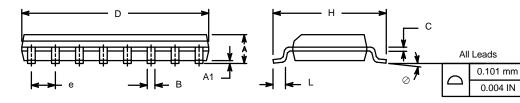


SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012



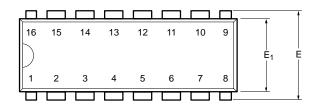
	MILLIM	IETERS	INC	HES						
Dim	Min	Max	Min	Max						
Α	1.35	1.75	0.053	0.069						
A ₁	0.10	0.20	0.004	0.008						
В	0.38	0.51	0.015	0.020						
С	0.18	0.23	0.007	0.009						
D	9.80	10.00	0.385	0.393						
E	3.80	4.00	0.149	0.157						
е	1.27	BSC	0.050	BSC						
Н	5.80	6.20	0.228	0.244						
L	0.50	0.93	0.020	0.037						
0	0°	8°	0°	8°						
ECN: S-0	ECN: S-03946—Rev. F. 09-Jul-01									

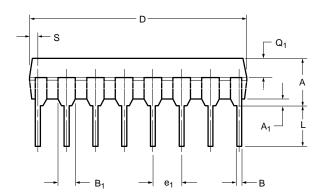
DWG: 5300

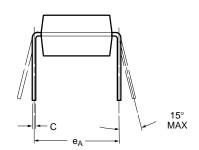




PDIP: 16-LEAD







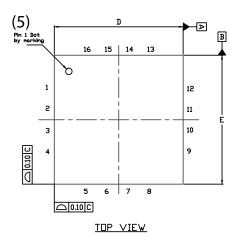
	MILLIN	IETERS	INC	HES				
Dim	Min	Max	Min	Max				
Α	3.81	5.08	0.150	0.200				
A ₁	0.38	1.27	0.015	0.050				
В	0.38	0.51	0.015	0.020				
B ₁	0.89	1.65	0.035	0.065				
С	0.20	0.30	0.008	0.012				
D	18.93	21.33	0.745	0.840				
E	7.62	8.26	0.300	0.325				
E ₁	5.59	7.11	0.220	0.280				
e ₁	2.29	2.79	0.090	0.110				
e _A	7.37	7.87	0.290	0.310				
L	2.79 3.81		0.110	0.150				
Q ₁	1.27	2.03	0.050	0.080				
S	0.38	1.52	.015	0.060				
ECN: S-03946—Rev. D, 09-Jul-01								

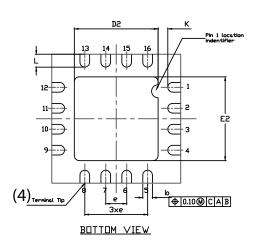
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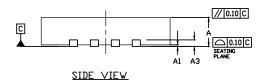
Document Number: 71261 www.vishay.com 06-Jul-01



QFN 4x4-16L Case Outline







	VARIATION 1			VARIATION 2								
DIM	МІ	MILLIMETERS ⁽¹⁾		INCHES		MILLIMETERS ⁽¹⁾		S ⁽¹⁾		INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3		0.20 ref.		0.008 ref.		0.20 ref.			0.008 ref.			
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D		4.00 BSC		0.157 BSC		4.00 BSC		0.157 BSC				
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
е	0.65 BSC)		0.026 BSC		0.65 BSC			0.026 BSC		
Е		4.00 BS0	0		0.157 BSC			4.00 BSC			0.157 BSC	
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
К		0.20 min.			0.008 min.			0.20 min.			0.008 min.	
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾		16			16 16		16					
Nd ⁽³⁾		4			4 4		4					
Ne ⁽³⁾		4			4		4 4					

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

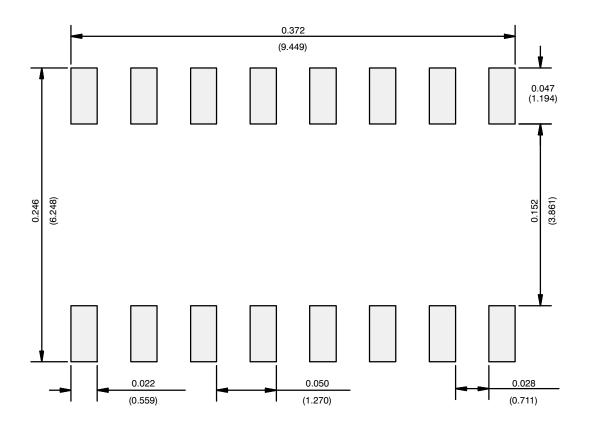
ECN: S13-0893-Rev. B, 22-Apr-13

DWG: 5890

Revision: 22-Apr-13



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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Vishay

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